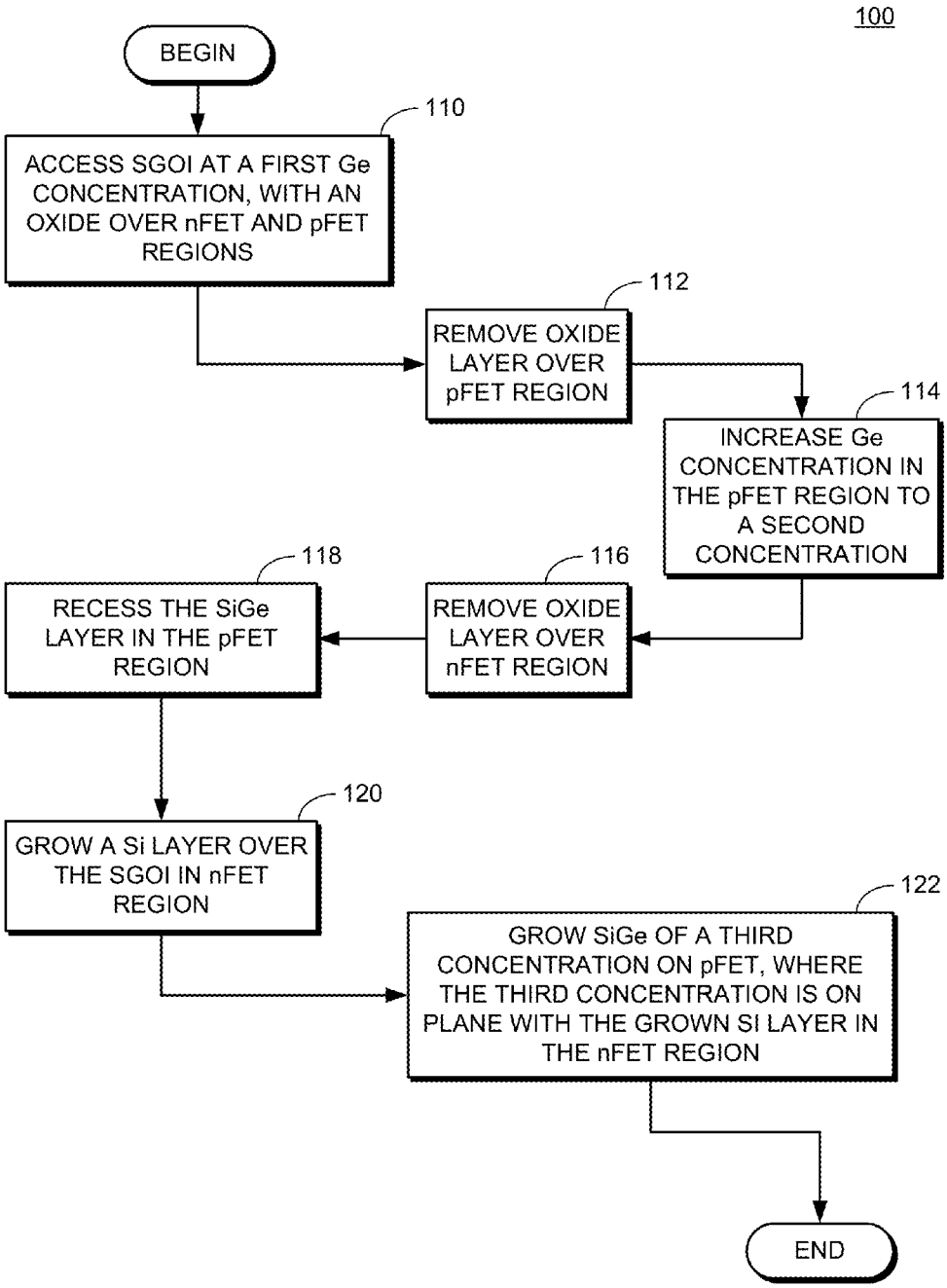
100
BEGIN
110
ACCESS SGOI AT A FIRST Ge CONCENTRATION, WITH AN OXIDE OVER nFET AND pFET REGIONS
112
REMOVE OXIDE LAYER OVER pFET REGION
114
INCREASE Ge CONCENTRATION IN THE pFET REGION TO A SECOND CONCENTRATION
116
REMOVE OXIDE LAYER OVER nFET REGION
118
RECESS THE SiGe LAYER IN THE pFET REGION
120
GROW A Si LAYER OVER THE SGOI IN nFET REGION
122
GROW SiGe OF A THIRD CONCENTRATION ON pFET, WHERE THE THIRD CONCENTRATION IS ON PLANE WITH THE GROWN SI LAYER IN THE nFET REGION
END

FIG. 1